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Title: SEMICONDUCTOR DEVICE WITH EPITAXIAL C49-TITANIUM SILICIDE (TISI₂) LAYER AND

METHOD FOR FABRICATING THE SAME

1st Named Inventor: Moon-Keun LEE

1st Named Inventor: Moon-Keun LEE Express Mail No.: EV339912925US

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FIG. 1A (PRIOR ART)

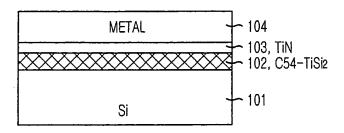
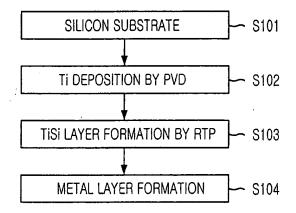


FIG. 1B (PRIOR ART)



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FIG. 2A

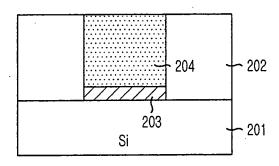
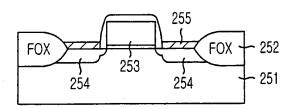


FIG. 2B



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FIG. 3A

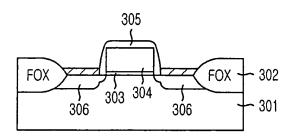
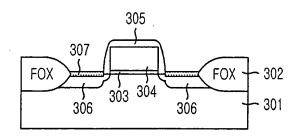


FIG. 3B



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FIG. 3C

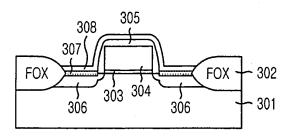
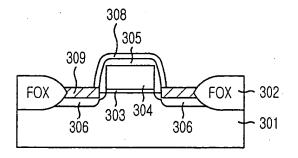


FIG. 3D



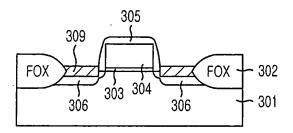
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Title: SEMICONDUCTOR DEVICE WITH EPITAXIAL C49-TITANIUM SILICIDE (TISI) LAYER

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FIG. 3E



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FIG. 4A

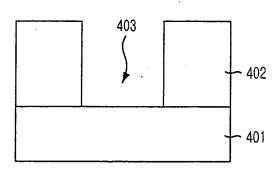
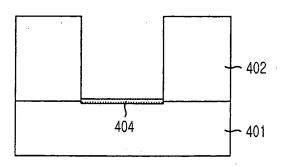


FIG. 4B



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FIG. 4C

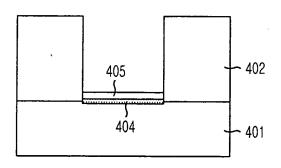
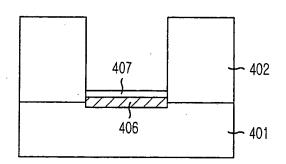


FIG. 4D



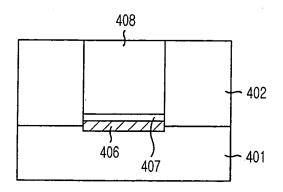
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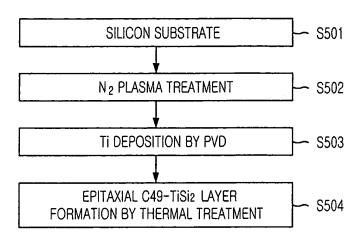
FIG. 4E



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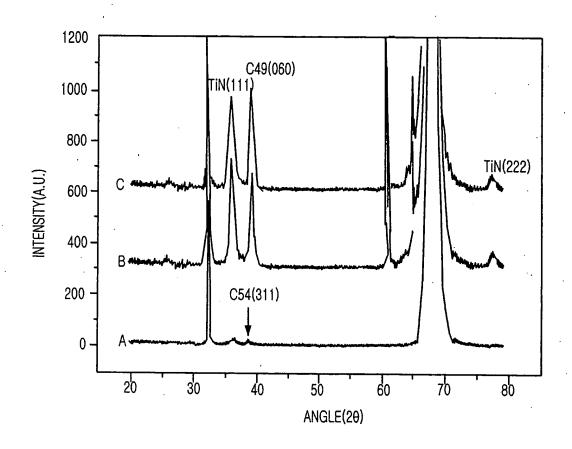
FIG. 5



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FIG. 6



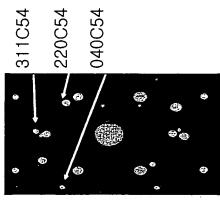
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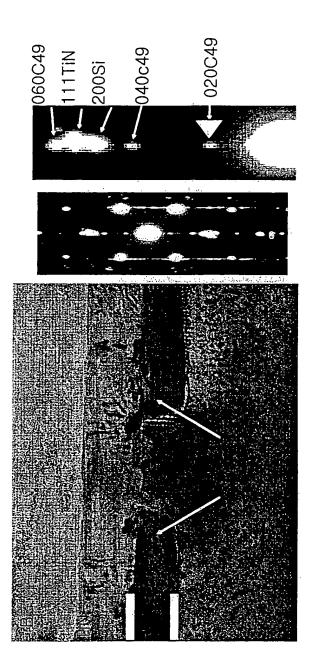


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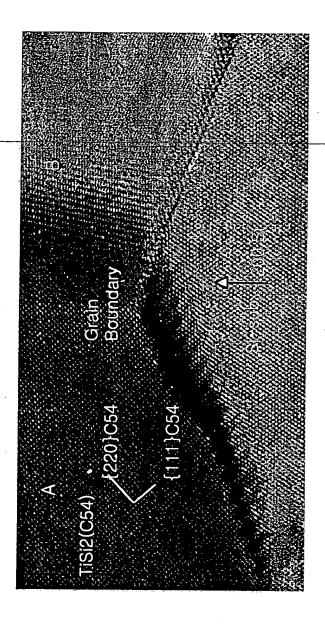
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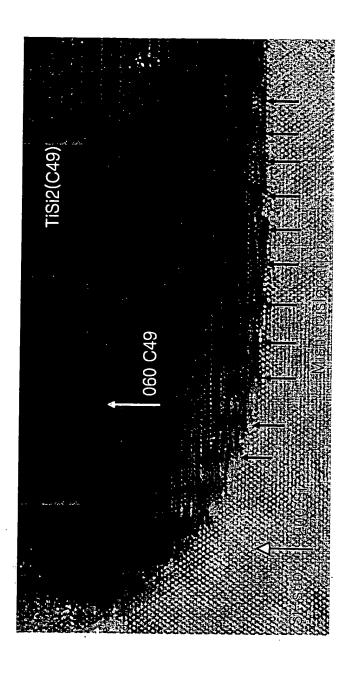


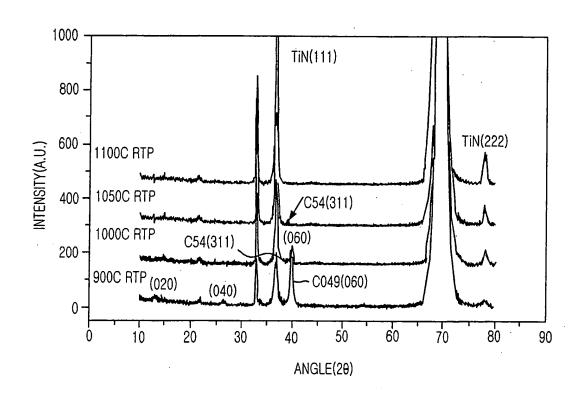
FIG. 8B

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FIG. 9



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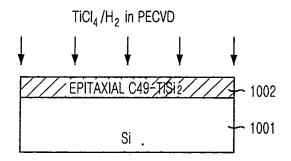
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FIG. 10

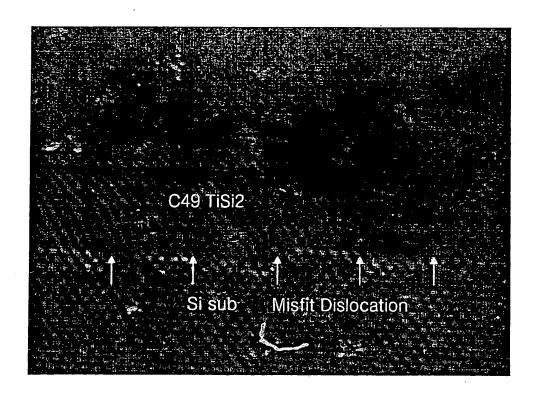


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FIG. 11A



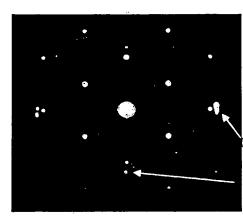
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FIG. 11B





C49 1.81A(2 0 0)

C49 2.29A(0 6 0)

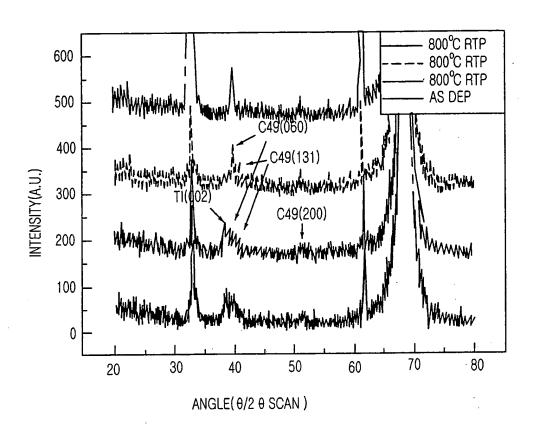
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FIG. 12



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FIG. 13A

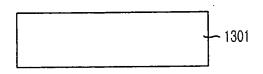


FIG. 13B

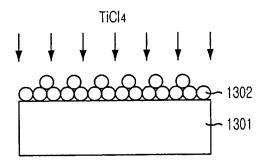
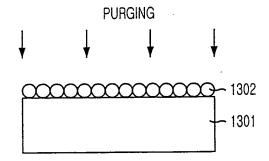


FIG. 13C



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FIG. 13D

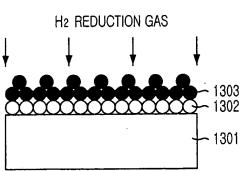


FIG. 13E

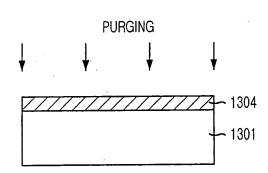


FIG. 13F

